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# MOS FIELD EFFECT TRANSISTOR $\mu$ PA1950

# P-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

### **DESCRIPTION**

The  $\mu$ PA1950 is a switching device which can be driven directly by a 1.8 V power source.

This device features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

### **FEATURES**

- 1.8 V drive available
- · Low on-state resistance

RDS(on)1 = 130 m $\Omega$  MAX. (VGS = -4.5 V, ID = -1.5 A)

RDS(on)2 = 176 m $\Omega$  MAX. (VGS = -3.0 V, ID = -1.5 A)

RDS(on)3 = 205 m $\Omega$  MAX. (VGS = -2.5 V, ID = -1.5 A)

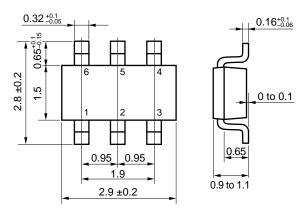
 $R_{DS(on)4} = 375 \text{ m}\Omega$  MAX. (Vgs = -1.8 V, ID = -1.0 A)

### **ORDERING INFORMATION**

PART NUMBER	PACKAGE
μΡΑ1950ΤΕ <sup>Note</sup>	SC-95 (Mini Mold Thin Type)

Note Marking: TM

### PACKAGE DRAWING (Unit: mm)



6: Drain1 4: Drain2 1: Gate1 3: Gate2 5: Source1 2: Source2

### **EQUIVALENT CIRCUIT**

### ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (Vgs = 0 V)	VDSS	-12	V
Gate to Source Voltage (Vps = 0 V)	Vgss	∓8.0	V
Drain Current (DC) (T <sub>A</sub> = 25°C)	ID(DC)	∓2.5	Α
Drain Current (pulse) Note1	D(pulse)	<b>∓7.0</b>	Α
Total Power Dissipation (2unit) Note2	P <sub>T1</sub>	1.15	W
Total Power Dissipation (1unit) Note2	P <sub>T2</sub>	0.57	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C

Drain 1 Drain 2 **★** Body Body Gate 1 Diode Gate 2 Diode Gate Gate Protection Protection Diode Diode Source 1 Source 2

**Notes 1.** PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1%

**2.** Mounted on FR-4 board,  $t \le 5$  sec.

**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

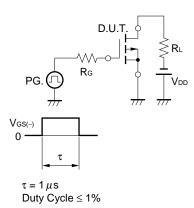
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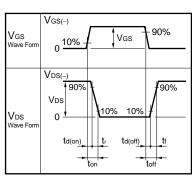


### **ELECTRICAL CHARACTERISTICS (TA = 25°C)**

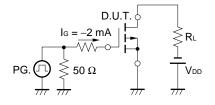
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	Ipss	V <sub>DS</sub> = -12 V, V <sub>GS</sub> = 0 V			-10	μΑ
Gate Leakage Current	lgss	$V_{GS} = \mp 8.0 \text{ V}, V_{DS} = 0 \text{ V}$			∓10	μΑ
Gate Cut-off Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -1.0 mA	-0.45		-1.5	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> = −10 V, I <sub>D</sub> = −1.5 A	1.0			S
Drain to Source On-state Resistance	RDS(on)1	Vgs = -4.5 V, ID = -1.5 A		105	130	mΩ
	RDS(on)2	$V_{GS} = -3.0 \text{ V}, I_{D} = -1.5 \text{ A}$		135	176	mΩ
	RDS(on)3	V <sub>G</sub> S = -2.5 V, I <sub>D</sub> = -1.5 A		160	205	mΩ
	RDS(on)4	V <sub>GS</sub> = -1.8 V, I <sub>D</sub> = -1.0 A		225	375	mΩ
Input Capacitance	Ciss	Vps = -10 V		220		pF
Output Capacitance	Coss	Vgs = 0 V		90		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		40		pF
Turn-on Delay Time	td(on)	$V_{DD} = -6.0 \text{ V}, \text{ ID} = -1.5 \text{ A}$		15		ns
Rise Time	tr	Vgs = -4.0 V		80		ns
Turn-off Delay Time	td(off)	$R_G = 10 \Omega$		150		ns
Fall Time	tf			120		ns
Total Gate Charge	Q <sub>G</sub>	V <sub>DD</sub> = -10 V		1.9		nC
Gate to Source Charge	Qgs	Vgs = -4.0 V		0.5		nC
Gate to Drain Charge	Q <sub>GD</sub>	I <sub>D</sub> = -2.5 A		0.7		nC
Body Diode Forward Voltage	VF(S-D)	IF = 2.5 A, VGS = 0 V		0.86		V

### **TEST CIRCUIT 1 SWITCHING TIME**

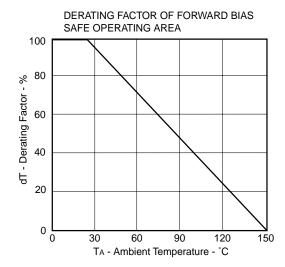


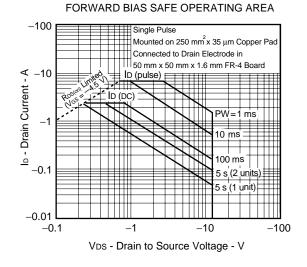


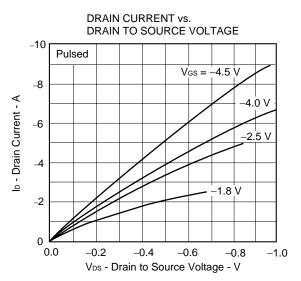
### **TEST CIRCUIT 2 GATE CHARGE**

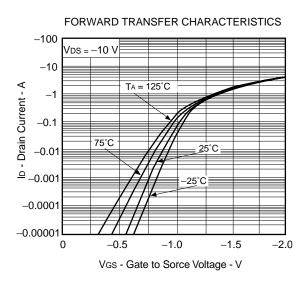


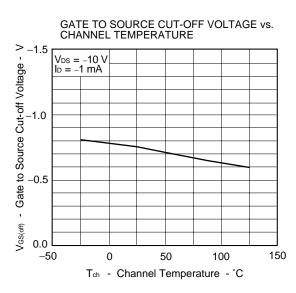
### TYPICAL CHARACTERISTICS (TA = 25°C)

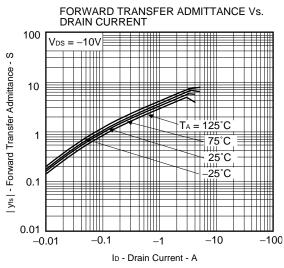




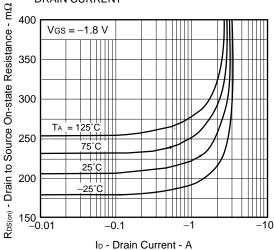




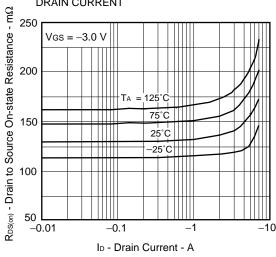




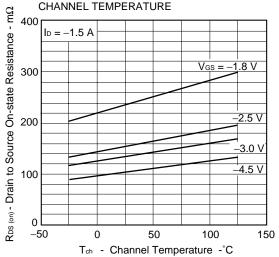
### DRAIN TO SOURCE ON-STATE RESISTANCE vs. **DRAIN CURRENT**



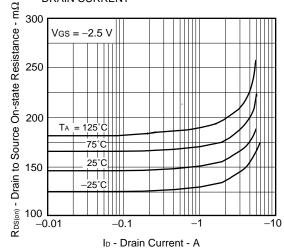
### DRAIN TO SOURCE ON-STATE RESISTANCE vs. **DRAIN CURRENT**



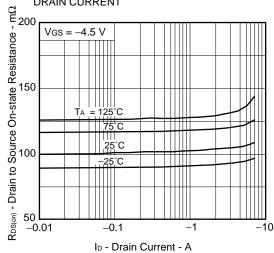
# DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



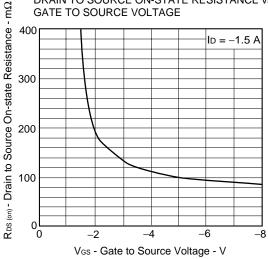
### DRAIN TO SOURCE ON-STATE RESISTANCE vs. **DRAIN CURRENT**

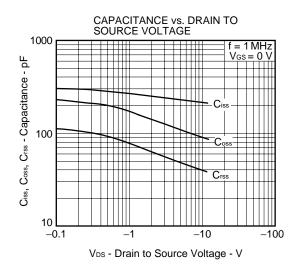


### DRAIN TO SOURCE ON-STATE RESISTANCE vs. **DRAIN CURRENT**



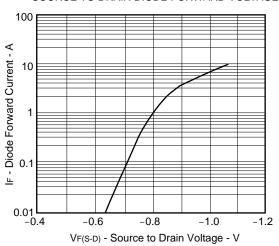
### DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

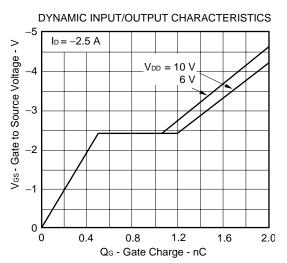




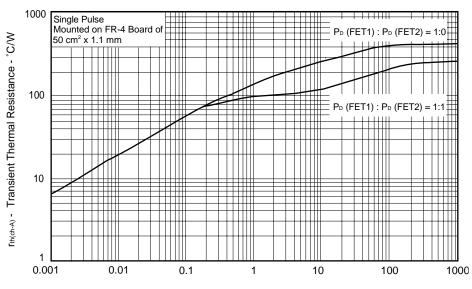
# SWITCHING CHARACTERISTICS 1000 SU La(off) 100 La(off) 10 La(off) VDD = -6.0 V VGS(on) = -4.0 V RG = 10 $\Omega$ 10 Ib - Drain Current - A

### SOURCE TO DRAIN DIODE FORWARD VOLTAGE





### TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



PW - Pulse Width - s

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[MEMO]

**NEC**  $\mu$ PA1950

[MEMO]

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